Low-Voltage CMOS Quad 2-Input Multiplexer

With 5.0 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX257 is a high performance, quad 2-input multiplexer with 3-state outputs operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX257 inputs to be safely driven from 5.0 V devices.

Four bits of data from two sources can be selected using the Select input. The four outputs present the selected data in the true (non-inverted) form. The outputs may be switched to a high impedance state by placing a logic HIGH on the Output Enable (\overline{OE}) input. Current drive capability is 24 mA at the outputs.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Interface Capability with 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - ♦ Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



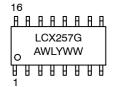
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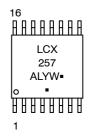


SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

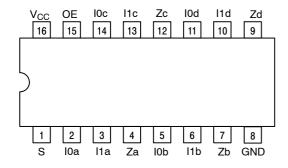


Figure 1. Pinout: 16-Lead Plastic Package (Top View)

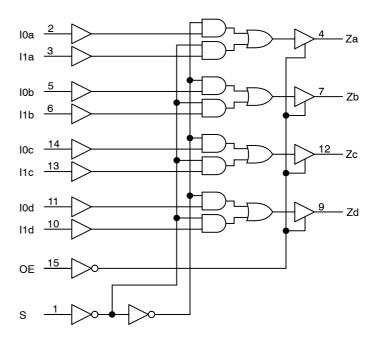


Figure 2. Logic Diagram

PIN NAMES

Pins	Function
l0n	Source 0 Data Inputs
l1n	Source 1 Data Inputs
ŌĒ	Output Enable Input
S	Select Input
Zn	Outputs

TRUTH TABLE

	Inp	Outputs		
ŌĒ	S	l0n	l1n	Zn
Н	Х	Х	Х	Z
L	Н	Х	L	L
L	Н	Х	Н	Н
L	L	L	Х	L
L	L	Н	Х	Н

H = High Voltage Level

L = Low Voltage Level

X = High or Low Voltage Level and Transitions are Acceptable
 Z = High Impedance State

For ICC reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{I} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{I} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Type	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State) (3-State)	0 0		V _{CC} 5.5	V
I _{OH}	$ \begin{array}{l} \mbox{HIGH Level Output Current} \\ \mbox{V}_{CC} = 3.0 \ \mbox{V} - 3.6 \ \mbox{V} \\ \mbox{V}_{CC} = 2.7 \ \mbox{V} - 3.0 \ \mbox{V} \\ \mbox{V}_{CC} = 2.3 \ \mbox{V} - 2.7 \ \mbox{V} \end{array} $			-24 -12 -8	mA
l _{OL}	LOW Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V V _{CC} = 2.3 V - 2.7 V			+24 +12 +8	mA
T _A	Operating Free-Air Temperature	-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX257DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LCX257DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LCX257DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = −40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Units
V _{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		
V _{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	1
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V _{CC} - 0.2		V
		V _{CC} = 2.3 V; I _{OH} = -8 mA	1.8		
		V _{CC} = 2.7 V; I _{OH} = -12 mA	2.2		1
		V _{CC} = 3.0 V; I _{OH} = -18 mA	2.4		1
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		1
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
I _{OZ}	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5	μА
I _{OFF}	Power Off Leakage Current	V _{CC} = 0, V _{IN} = 5.5 V or V _{OUT} = 5.5 V		10	μΑ
I _{IN}	Input Leakage Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		±5	μΑ
I _{CC}	Quiescent Supply Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS $t_R=t_F$ = 2.5 ns; R_L = 500 Ω

					Lin	nits			
				$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$					
			V _{CC} = 3.3	3 V ± 0.3 V	V _{CC} =	2.7 V	V _{CC} = 2.5	V ± 0.2 V	
			C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t _{PLH} t _{PHL}	Propagation Delay In to Zn	1	1.5 1.5	6.0 6.0	1.5 1.5	6.5 6.5	1.5 1.5	7.2 7.2	ns
t _{PLH} t _{PHL}	Propagation Delay S to Zn	1, 2	1.5 1.5	7.0 7.0	1.5 1.5	8.5 8.5	1.5 1.5	9.1 9.1	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	3	1.5 1.5	7.0 7.0	1.5 1.5	8.5 8.5	1.5 1.5	9.1 9.1	ns
t_{PHZ}	Output Disable Time from High and Low Level	3	1.5 1.5	5.5 5.5	1.5 1.5	6.0 6.0	1.5 1.5	6.6 6.6	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

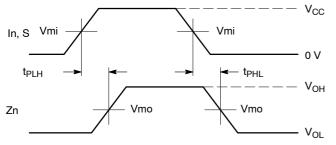
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V} $ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V} $ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		-0.8 -0.6		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	7	pF
C _{I/O}	Input/Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



S Vmi Vmi 0 V

tpLH Voh

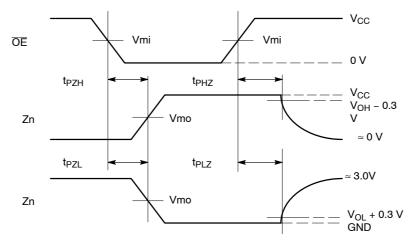
Vmo Vmo Vmo

 V_{CC}

WAVEFORM 1 - NON-INVERTING PROPAGATION DELAYS

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1.0 MHz; t_W = 500 ns

WAVEFORM 2 – INVERTING PROPAGATION DELAYS $t_R=t_F=2.5$ ns, 10% to 90%; f = 1.0 MHz; $t_W=500$ ns



WAVEFORM 3 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1.0 \text{ MHz}; t_W = 500 \text{ ns}$

	Vcc				
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V		
Vmi	1.5 V	1.5 V	Vcc/2		
Vmo	1.5 V	1.5 V	Vcc/2		
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V		
V _{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 0.15 V		

Figure 3. AC Waveforms



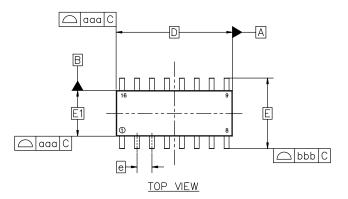


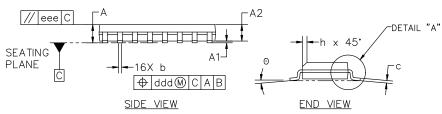
SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

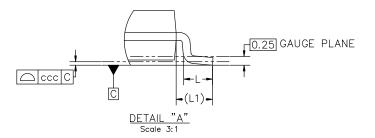
DATE 29 MAY 2024

NOTES:

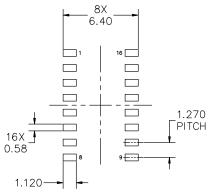
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS						
DIM	MIN	NOM	MAX			
Α	1.35	1.55	1.75			
A1	0.00	0.05	0.10			
A2	1.35	1.50	1.65			
Ь	0.35	0.42	0.49			
С	0.19	0.22	0.25			
D		9.90 BSC				
E		6.00 BSC				
E1		3.90 BSC				
е		1.27 BSC				
h	0.25		0.50			
L	0.40	0.83	1.25			
L1		1.05 REF				
Θ	0,		7°			
TOLERAN	CE OF FC	RM AND	POSITION			
aaa	0.10					
bbb	0.20					
ccc	0.10					
ddd		0.25				
eee		0.10				



RECOMMENDED MOUNTING FOOTPRINT

*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

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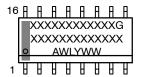
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SOIC-16 9.90x3.90x1.50 1.27P

CASE 751B ISSUE L

DATE 29 MAY 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

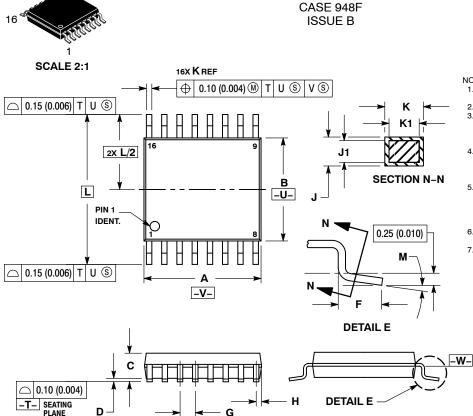
STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	,	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
4.	,	4.	CATHODE	4.			
5.	DRAIN, #3	5.		5.	COMMON DRAIN (OUTPUT)		
6.	DRAIN, #3	6.		6.	COMMON DRAIN (OUTPUT)		
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPUT)		
8.	DRAIN, #4		CATHODE	8.	SOURCE P-CH		
	GATE, #4		ANODE	9.	SOURCE P-CH		
10.	SOURCE, #4		ANODE	10.			
11.	GATE, #3		ANODE	11.			
12		12	ANODE	12.			
	SOURCE, #3		-				
13.	GATE, #2	13.	ANODE	13.			
13. 14.	GATE, #2 SOURCE, #2	13. 14.	ANODE	14.	COMMON DRAIN (OUTPUT)		
13. 14. 15.	GATE, #2 SOURCE, #2 GATE, #1	13. 14. 15.	ANODE ANODE	14. 15.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
13. 14.	GATE, #2 SOURCE, #2	13. 14.	ANODE	14.	COMMON DRAIN (OUTPUT)		

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DATE 19 OCT 2006





TSSOP-16 WB

NOTES:

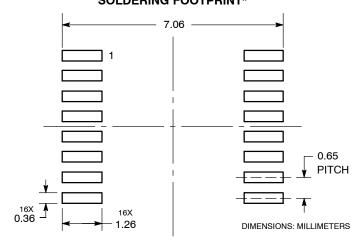
- DIMENSIONING AND TOLERANCING PER
 ANSI V14 5M 1982
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- INTERLEAD FLASH ON PHOTHOSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0 °	8°	0 °	8 °	

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week G or = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

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